

# BCP68; BC868; BC68PA

20 V, 2 A NPN medium power transistors

Rev. 8 — 18 October 2011

Product data sheet

## 1. Product profile

### 1.1 General description

NPN medium power transistor series in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number <sup>[1]</sup>	Package			PNP complement
	NXP	JEITA	JEDEC	
BCP68	SOT223	SC-73	-	BCP69
BC868	SOT89	SC-62	TO-243	BC869
BC68PA	SOT1061	-	-	BC69PA

[1] Valid for all available selection groups.

### 1.2 Features and benefits

- High current
- Two current gain selections
- High power dissipation capability
- Exposed heatsink for excellent thermal and electrical conductivity (SOT89, SOT1061)
- Leadless very small SMD plastic package with medium power capability (SOT1061)
- AEC-Q101 qualified

### 1.3 Applications

- Linear voltage regulators
- Power management
- Low-side switches
- MOSFET drivers
- Battery-driven devices
- Amplifiers

### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	20	V
$I_C$	collector current		-	-	2	A
$I_{CM}$	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	3	A



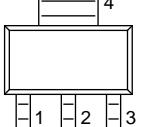
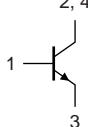
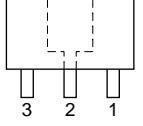
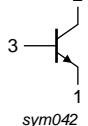
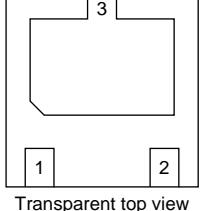
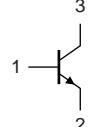
**Table 2.** Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$h_{FE}$	DC current gain	$V_{CE} = 1 \text{ V}; I_C = 500 \text{ mA}$	[1] 85	-	375	
	$h_{FE}$ selection -25	$V_{CE} = 1 \text{ V}; I_C = 500 \text{ mA}$	[1] 160	-	375	

[1] Pulse test:  $t_p \leq 300 \mu\text{s}$ ;  $\delta = 0.02$ .

## 2. Pinning information

**Table 3.** Pinning

Pin	Description	Simplified outline	Graphic symbol
<b>SOT223</b>			
1	base		
2	collector		
3	emitter		
4	collector	 sym016	 sym016
<b>SOT89</b>			
1	emitter		
2	collector		
3	base	 sym042	 sym042
<b>SOT1061</b>			
1	base		
2	emitter		
3	collector	 Transparent top view	 sym021

### 3. Ordering information

**Table 4. Ordering information**

Type number <sup>[1]</sup>	Package		
	Name	Description	Version
BCP68	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223
BC868	SC-62	plastic surface-mounted package; exposed die pad for good heat transfer; 3 leads	SOT89
BC68PA	HUSON3	plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 2 × 2 × 0.65 mm	SOT1061

[1] Valid for all available selection groups.

### 4. Marking

**Table 5. Marking codes**

Type number	Marking code
BCP68	BCP68
BCP68-25	BCP68/25
BC868	CAC
BC868-25	CDC
BC68PA	AR
BC68-25PA	AS

## 5. Limiting values

**Table 6. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter	-	32	V
$V_{CEO}$	collector-emitter voltage	open base	-	20	V
$V_{EBO}$	emitter-base voltage	open collector	-	5	V
$I_C$	collector current		-	2	A
$I_{CM}$	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	3	A
$I_B$	base current		-	0.4	A
$I_{BM}$	peak base current	single pulse; $t_p \leq 1 \text{ ms}$	-	0.4	A
$P_{tot}$	total power dissipation	$T_{amb} \leq 25 \text{ }^{\circ}\text{C}$			
	BCP68		[1]	-	0.65 W
			[2]	-	1.00 W
			[3]	-	1.35 W
	BC868		[1]	-	0.50 W
			[2]	-	0.95 W
			[3]	-	1.35 W
	BC68PA		[1]	-	0.42 W
			[2]	-	0.83 W
			[3]	-	1.10 W
			[4]	-	0.81 W
			[5]	-	1.65 W
$T_j$	junction temperature		-	150	$^{\circ}\text{C}$
$T_{amb}$	ambient temperature		-55	+150	$^{\circ}\text{C}$
$T_{stg}$	storage temperature		-65	+150	$^{\circ}\text{C}$

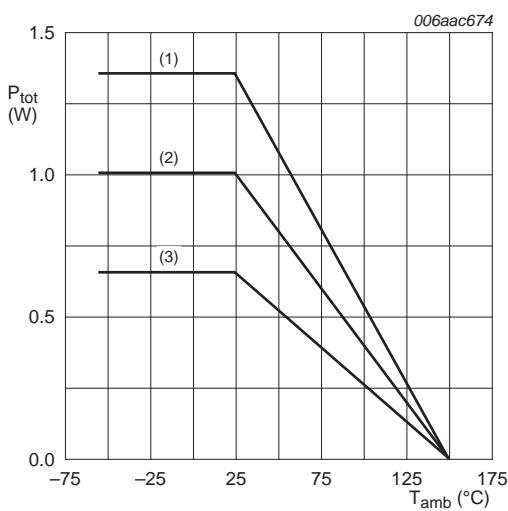
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1  $\text{cm}^2$ .

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6  $\text{cm}^2$ .

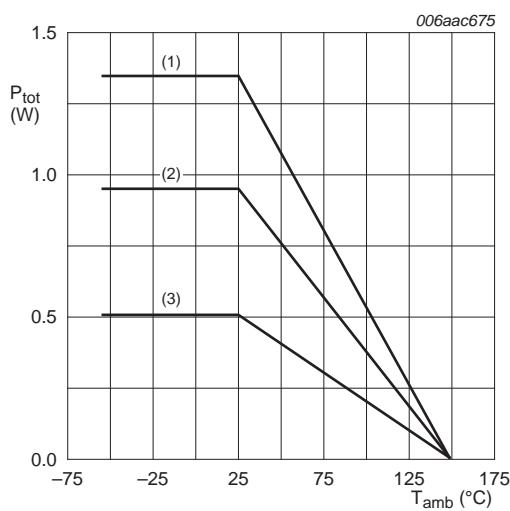
[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1  $\text{cm}^2$ .



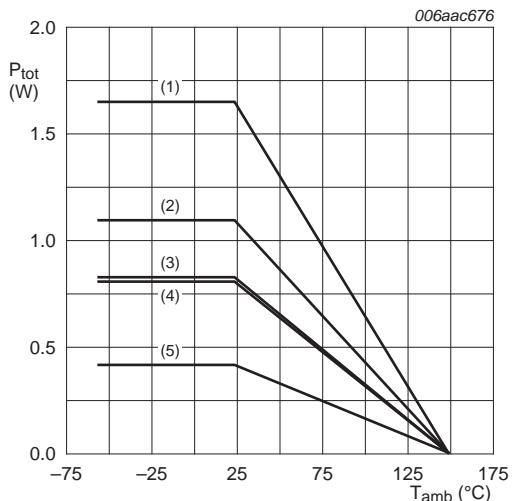
- (1) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (2) FR4 PCB, mounting pad for collector 1 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

Fig 1. Power derating curves SOT223



- (1) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (2) FR4 PCB, mounting pad for collector 1 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

Fig 2. Power derating curves SOT89



- (1) FR4 PCB, 4-layer copper, mounting pad for collector 1 cm<sup>2</sup>
- (2) FR4 PCB, single-sided copper, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, single-sided copper, mounting pad for collector 1 cm<sup>2</sup>
- (4) FR4 PCB, 4-layer copper, standard footprint
- (5) FR4 PCB, single-sided copper, standard footprint

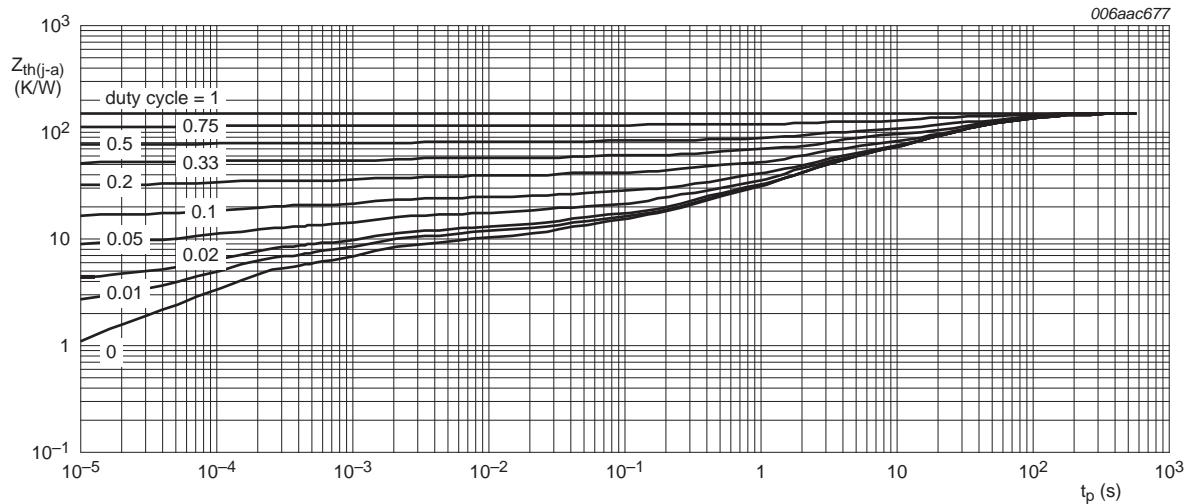
Fig 3. Power derating curves SOT1061

## 6. Thermal characteristics

**Table 7. Thermal characteristics**

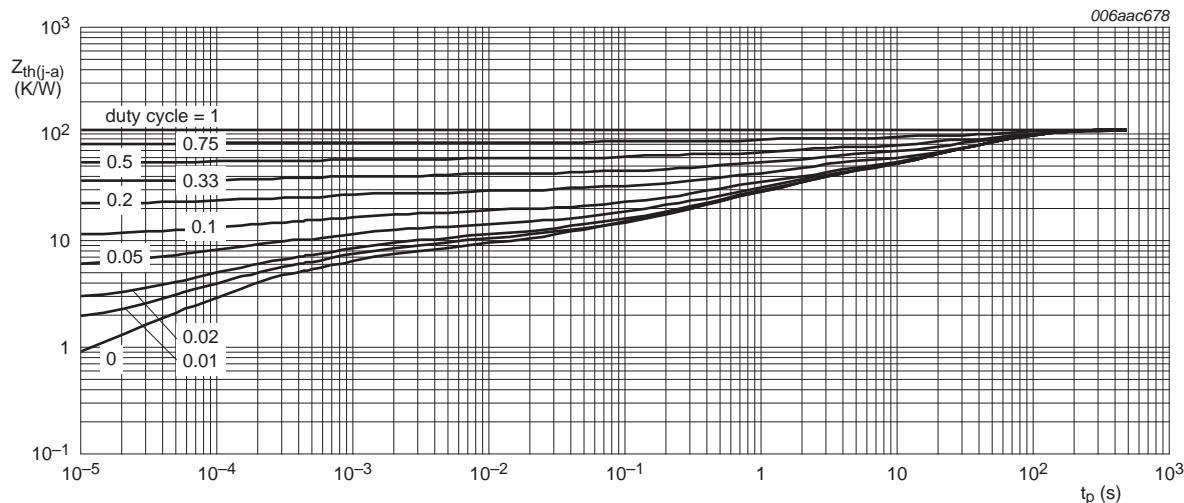
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
BCP68			[1]	-	192	K/W
			[2]	-	125	K/W
			[3]	-	93	K/W
BC868			[1]	-	250	K/W
			[2]	-	132	K/W
			[3]	-	93	K/W
BC68PA			[1]	-	298	K/W
			[2]	-	151	K/W
			[3]	-	114	K/W
			[4]	-	154	K/W
			[5]	-	76	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point					
BCP68			-	-	16	K/W
			-	-	16	K/W
			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.



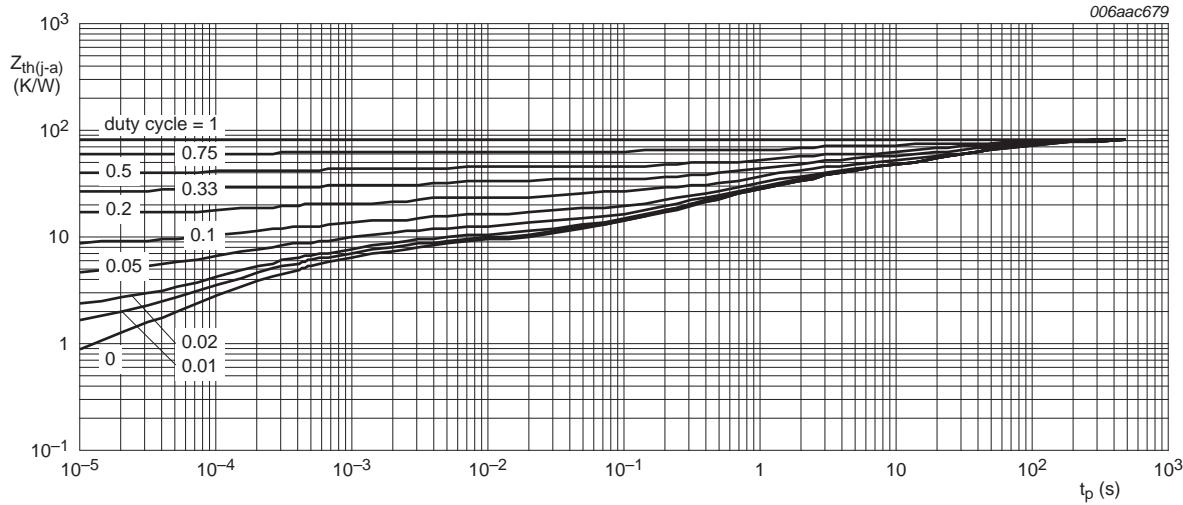
FR4 PCB, standard footprint

**Fig 4.** Transient thermal impedance from junction to ambient as a function of pulse duration for SOT223; typical values



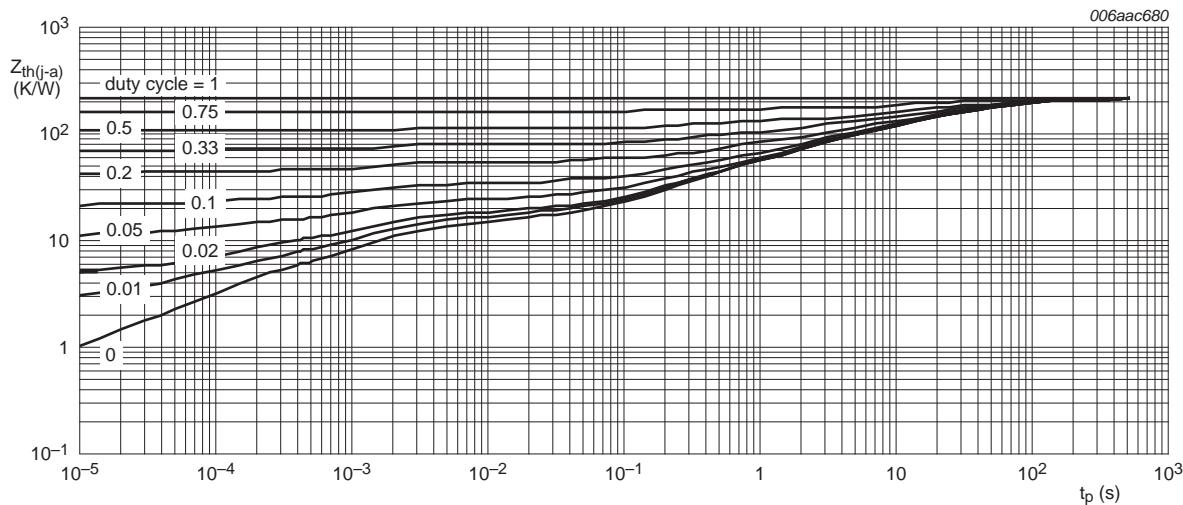
FR4 PCB, mounting pad for collector 1 cm<sup>2</sup>

**Fig 5.** Transient thermal impedance from junction to ambient as a function of pulse duration for SOT223; typical values



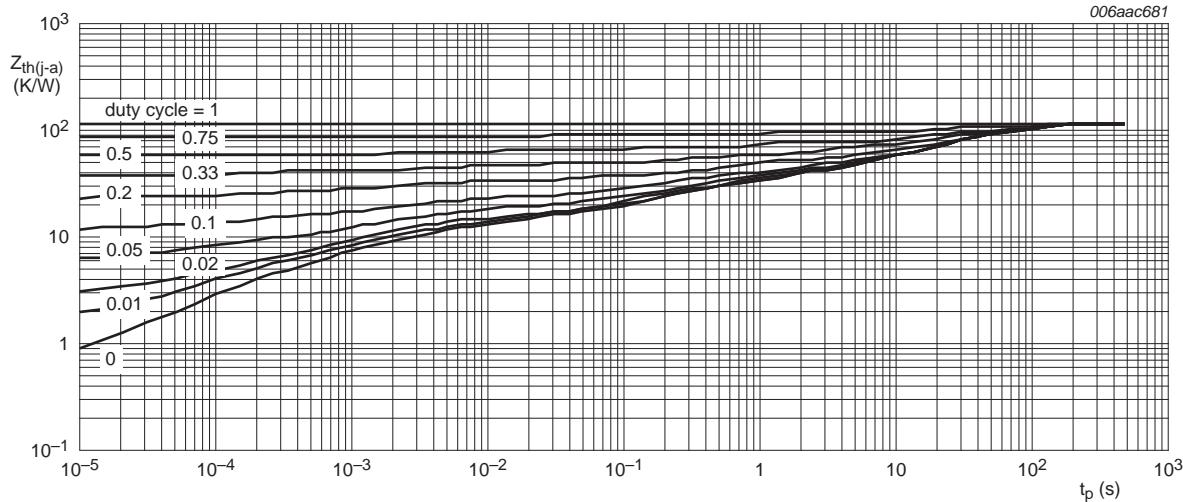
FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>

**Fig 6. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT223; typical values**



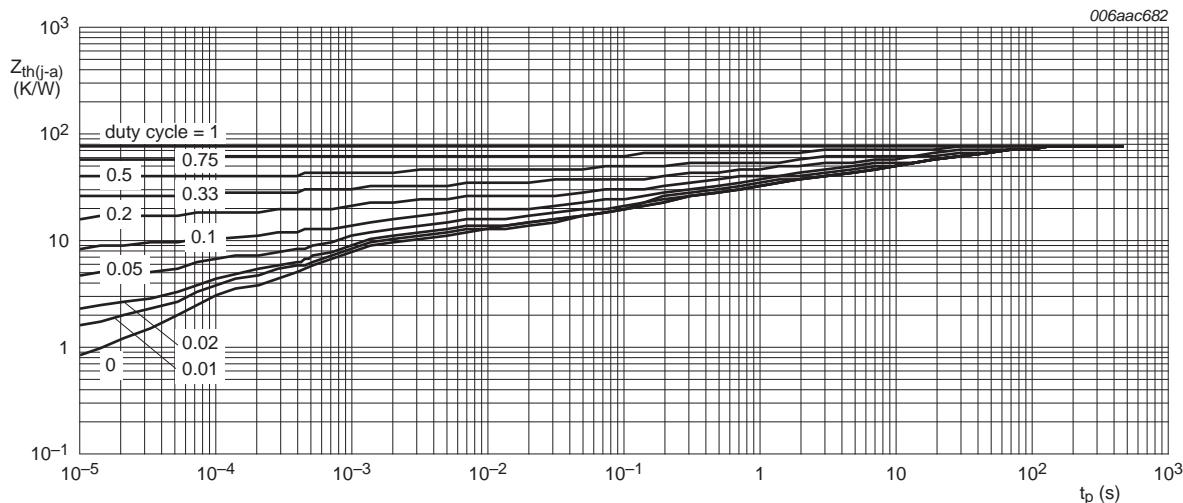
FR4 PCB, standard footprint

**Fig 7. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT89; typical values**



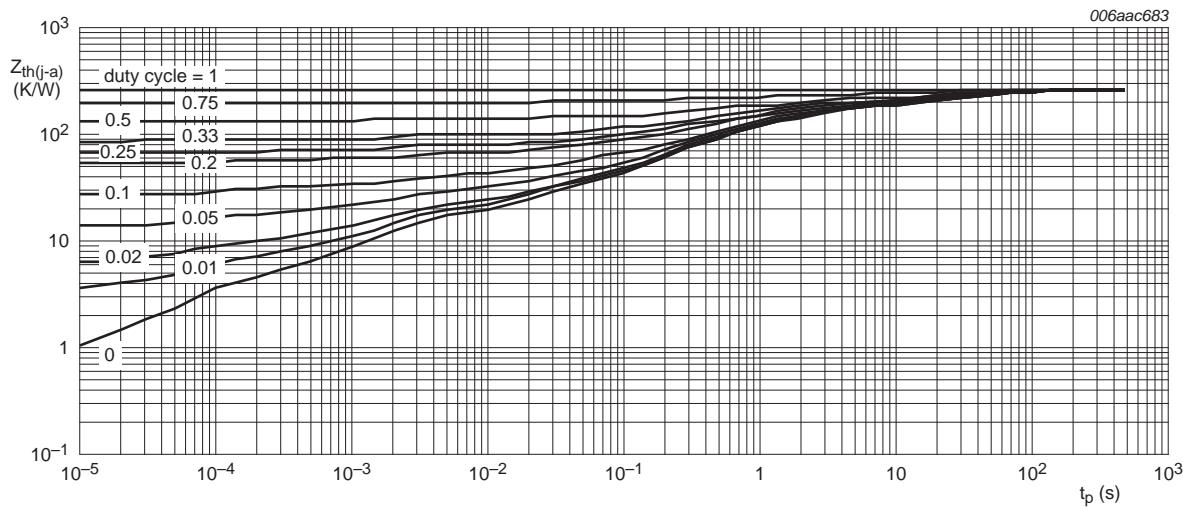
FR4 PCB, mounting pad for collector 1 cm<sup>2</sup>

**Fig 8.** Transient thermal impedance from junction to ambient as a function of pulse duration for SOT89; typical values



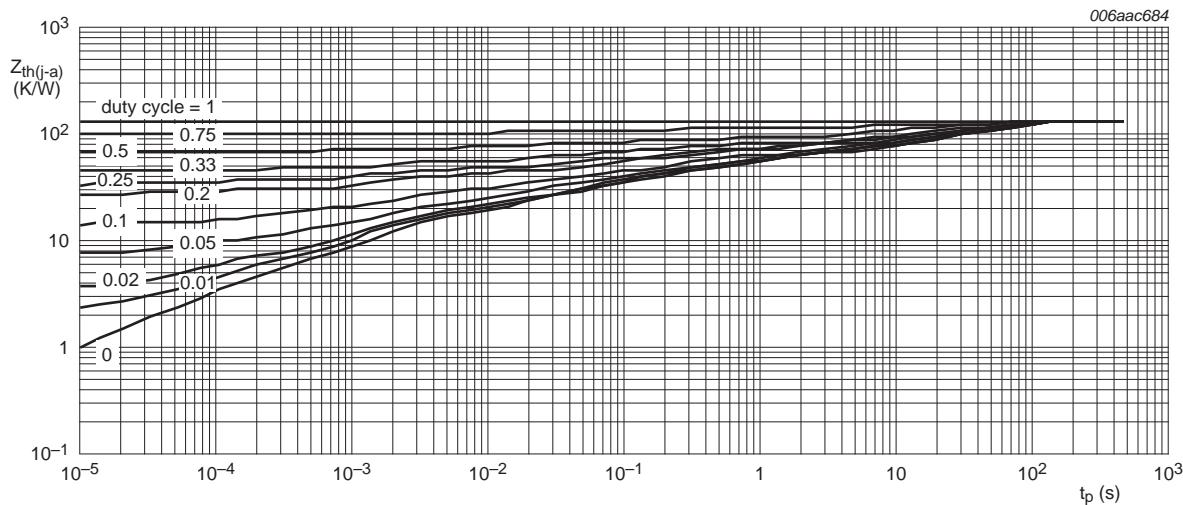
FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>

**Fig 9.** Transient thermal impedance from junction to ambient as a function of pulse duration for SOT89; typical values



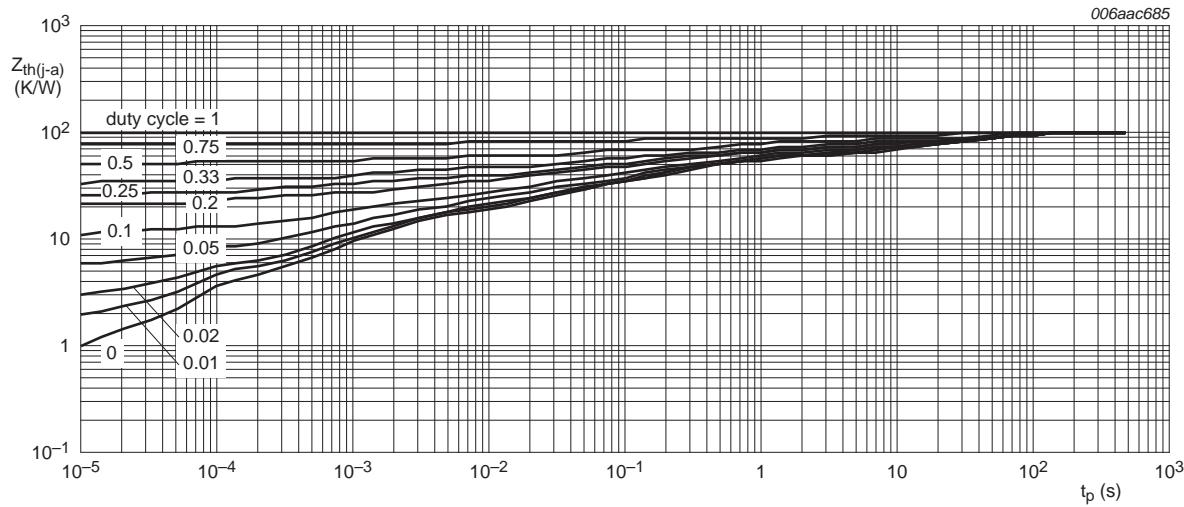
FR4 PCB, single-sided copper, standard footprint

**Fig 10. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT1061; typical values**



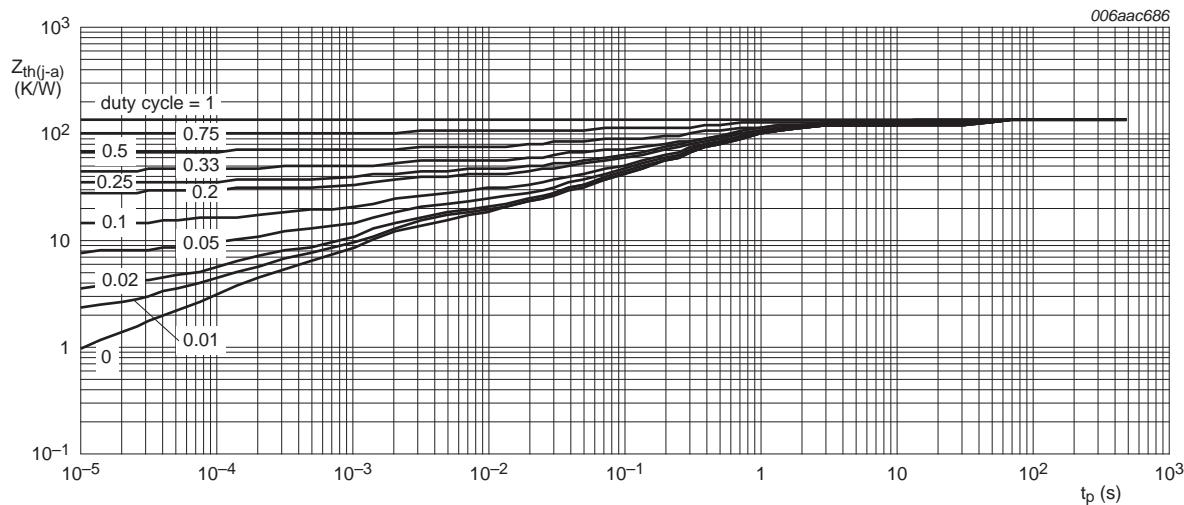
FR4 PCB, single-sided copper, mounting pad for collector 1 cm<sup>2</sup>

**Fig 11. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT1061; typical values**



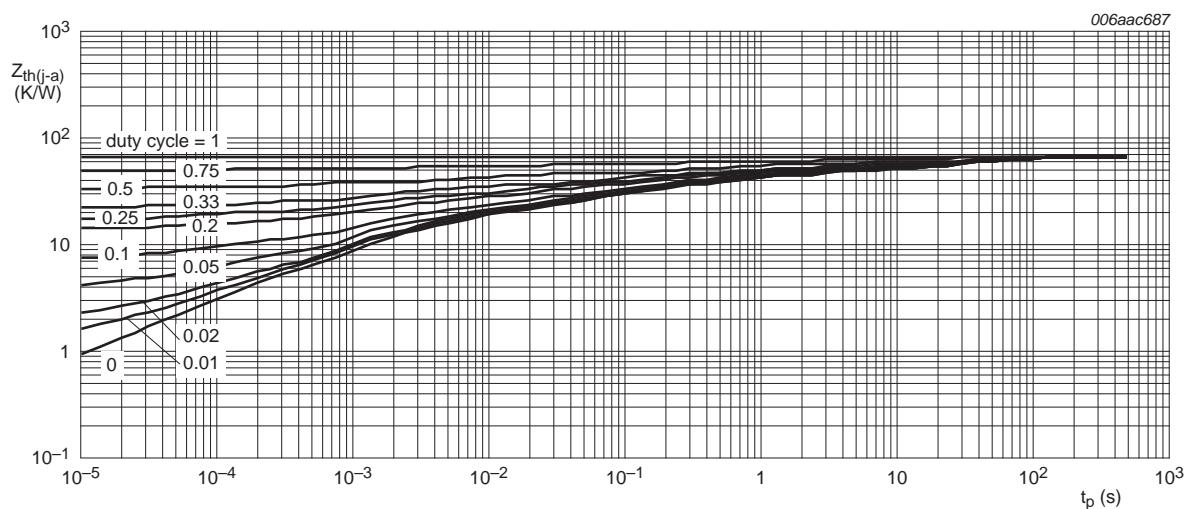
FR4 PCB, single-sided copper, mounting pad for collector 6 cm<sup>2</sup>

**Fig 12. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT1061; typical values**



FR4 PCB, 4-layer copper, standard footprint

**Fig 13. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT1061; typical values**



FR4 PCB, 4-layer copper, mounting pad for collector  $1 \text{ cm}^2$

**Fig 14. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT1061; typical values**

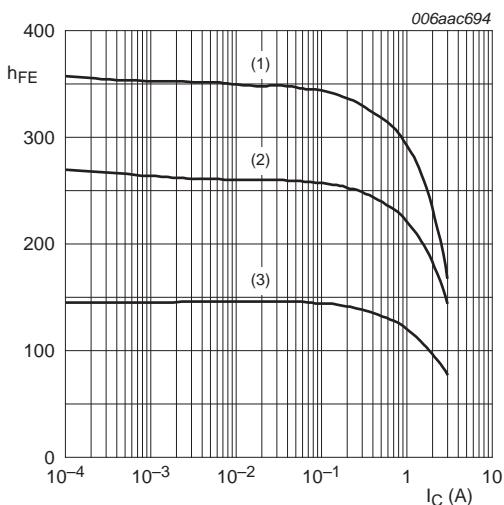
## 7. Characteristics

**Table 8. Characteristics**

$T_{amb} = 25^\circ\text{C}$  unless otherwise specified.

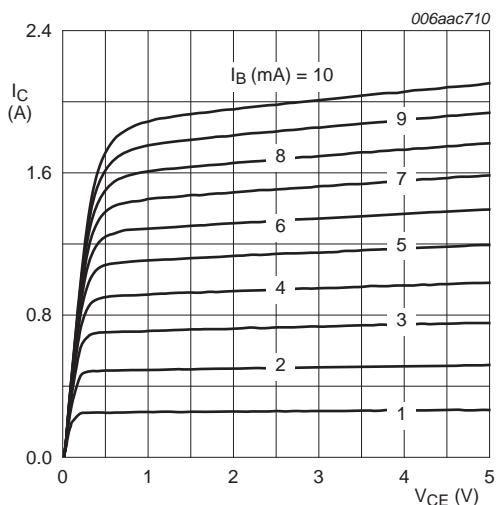
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 25 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
		$V_{CB} = 25 \text{ V}; I_E = 0 \text{ A}; T_j = 150^\circ\text{C}$	-	-	10	µA
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}$	-	-	100	nA
$h_{FE}$	DC current gain	$V_{CE} = 10 \text{ V}$				
		$I_C = 5 \text{ mA}$	50	-	-	
	DC current gain	$V_{CE} = 1 \text{ V}$				
		$I_C = 500 \text{ mA}$	[1] 85	-	375	
		$I_C = 1 \text{ A}$	[1] 60	-	-	
		$I_C = 2 \text{ A}$	[1] 40	-	-	
$V_{CEsat}$	DC current gain	$V_{CE} = 1 \text{ V}$				
	$h_{FE}$ selection -25	$I_C = 500 \text{ mA}$	[1] 160	-	375	
	collector-emitter saturation voltage	$I_C = 1 \text{ A}; I_B = 100 \text{ mA}$	[1] -	-	0.5	V
$V_{BE}$	base-emitter voltage	$I_C = 2 \text{ A}; I_B = 200 \text{ mA}$	[1] -	-	0.6	V
		$V_{CE} = 10 \text{ V}; I_C = 5 \text{ mA}$	[1] -	-	0.7	V
$C_c$	collector capacitance	$V_{CE} = 1 \text{ V}; I_C = 1 \text{ A}$	[1] -	-	1	V
		$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A}; f = 1 \text{ MHz}$	-	22	-	pF
$f_T$	transition frequency	$V_{CE} = 5 \text{ V}; I_C = 50 \text{ mA}; f = 100 \text{ MHz}$	40	170	-	MHz

[1] Pulse test:  $t_p \leq 300 \mu\text{s}$ ;  $\delta = 0.02$ .



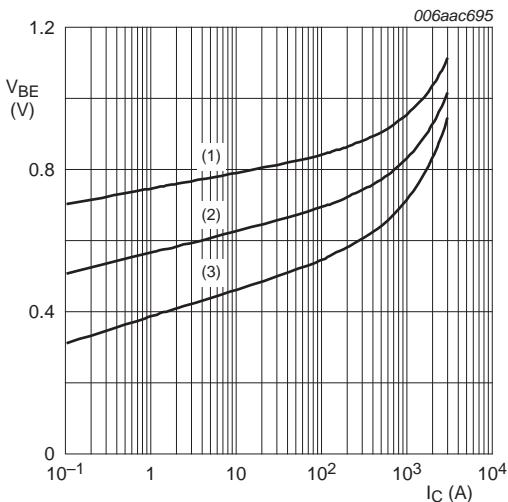
- $V_{CE} = 1$  V
- (1)  $T_{amb} = 100$  °C
  - (2)  $T_{amb} = 25$  °C
  - (3)  $T_{amb} = -55$  °C

**Fig 15.** DC current gain as a function of collector current; typical values



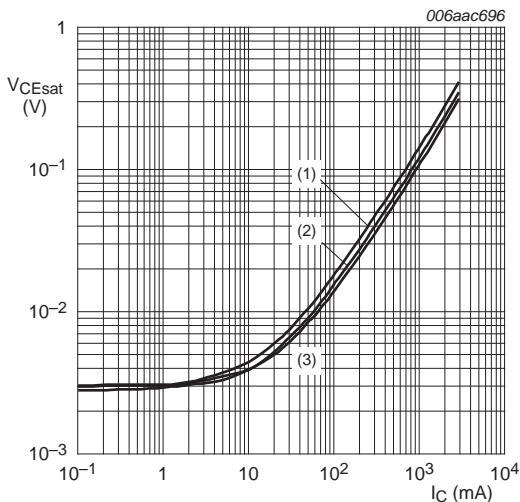
$T_{amb} = 25$  °C

**Fig 16.** Collector current as a function of collector-emitter voltage; typical values



- $V_{CE} = 1$  V
- (1)  $T_{amb} = -55$  °C
  - (2)  $T_{amb} = 25$  °C
  - (3)  $T_{amb} = 100$  °C

**Fig 17.** Base-emitter voltage as a function of collector current; typical values



- $I_C/I_B = 10$
- (1)  $T_{amb} = 100$  °C
  - (2)  $T_{amb} = 25$  °C
  - (3)  $T_{amb} = -55$  °C

**Fig 18.** Collector-emitter saturation voltage as a function of collector current; typical values

## 8. Test information

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 9. Package outline

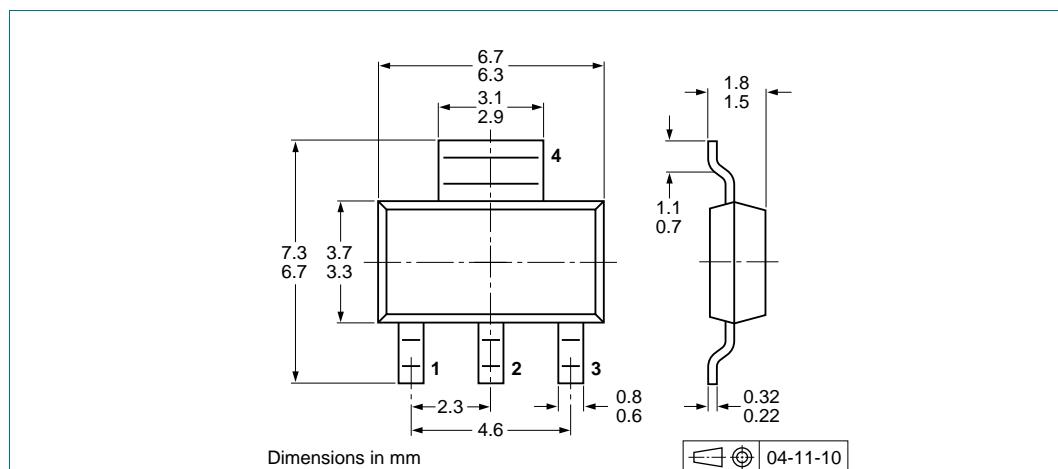


Fig 19. Package outline SOT223 (SC-73)

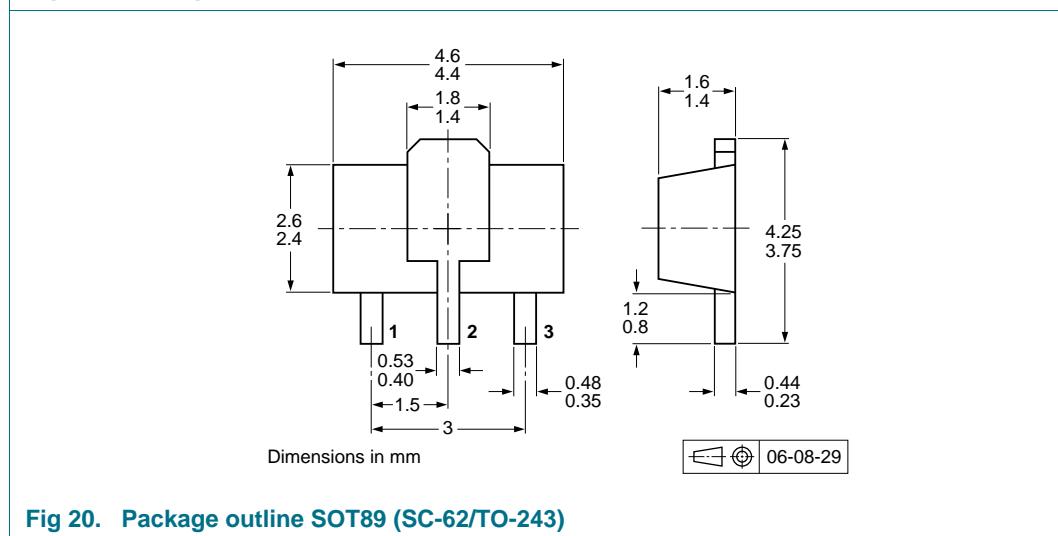


Fig 20. Package outline SOT89 (SC-62/TO-243)

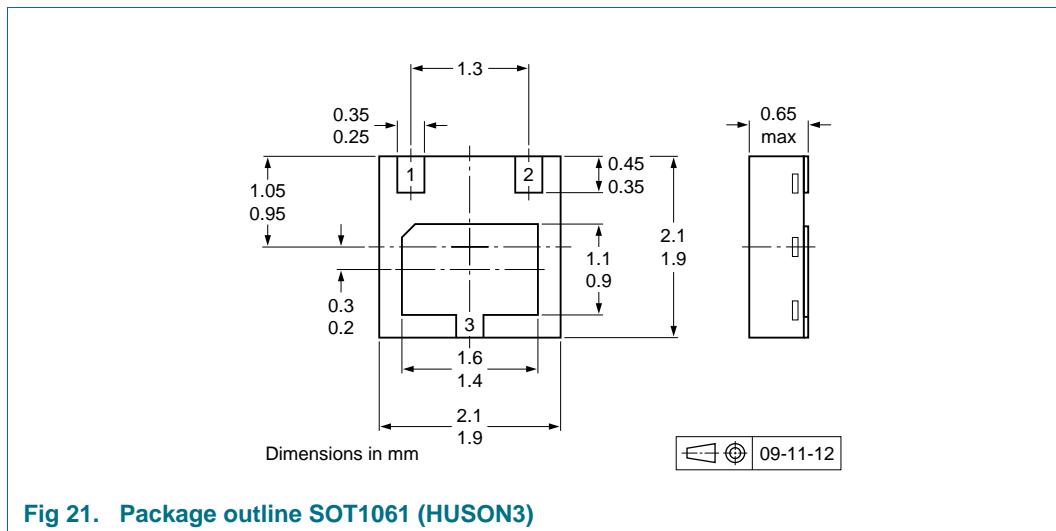


Fig 21. Package outline SOT1061 (HUSON3)

## 10. Packing information

**Table 9. Packing methods**

The indicated -xxx are the last three digits of the 12NC ordering code.<sup>[1]</sup>

Type number <sup>[2]</sup>	Package	Description	Packing quantity		
			1000	3000	4000
BCP68	SOT223	8 mm pitch, 12 mm tape and reel	-115	-	-135
BC868	SOT89	8 mm pitch, 12 mm tape and reel; T1	[3]	-115	-
		8 mm pitch, 12 mm tape and reel; T3	[4]	-146	-
BC68PA	SOT1061	4 mm pitch, 8 mm tape and reel	-	-115	-

[1] For further information and the availability of packing methods, see [Section 14](#).

[2] Valid for all available selection groups.

[3] T1: normal taping

[4] T3: 90° rotated taping

## 11. Soldering

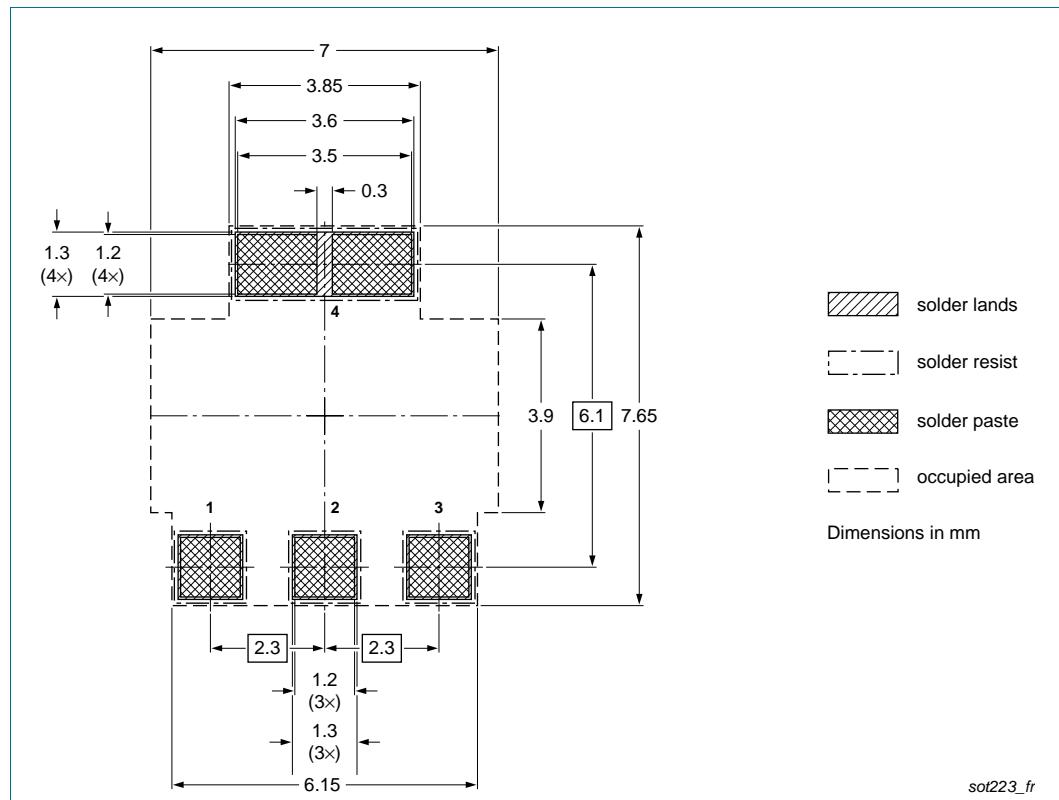


Fig 22. Reflow soldering footprint SOT223 (SC-73)

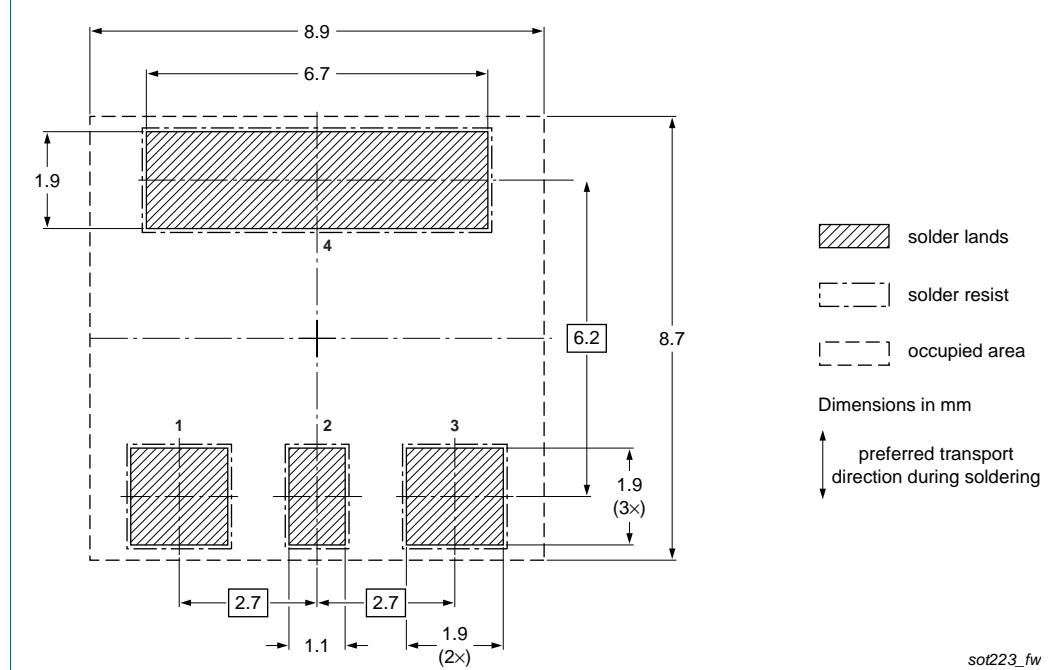


Fig 23. Wave soldering footprint SOT223 (SC-73)

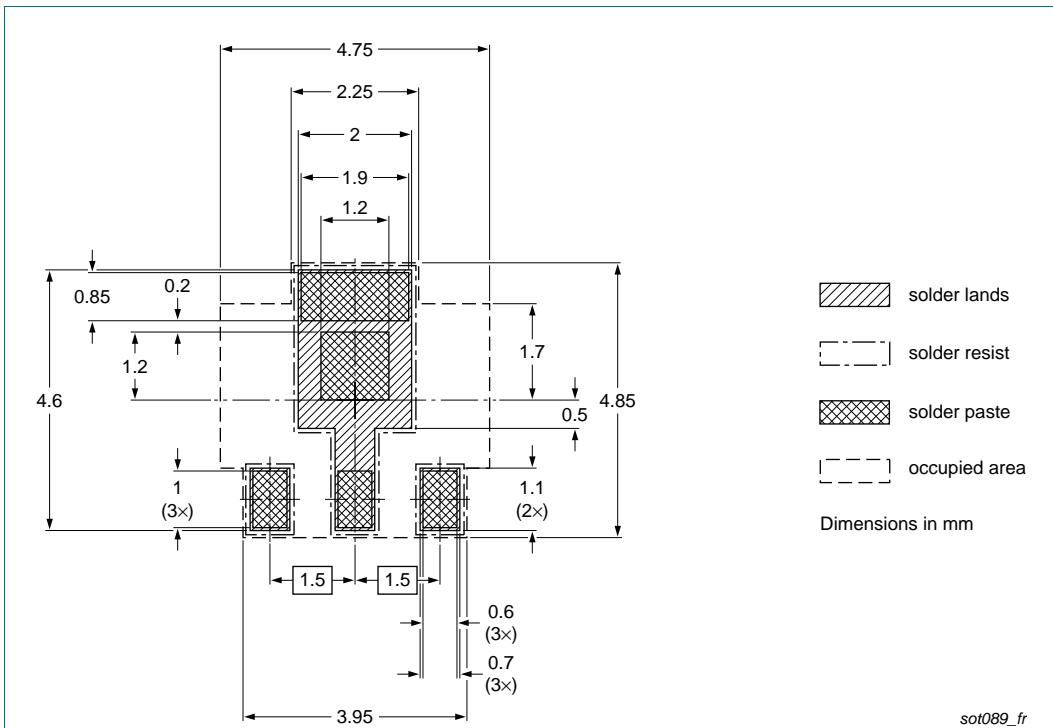


Fig 24. Reflow soldering footprint SOT89 (SC-62/TO-243)

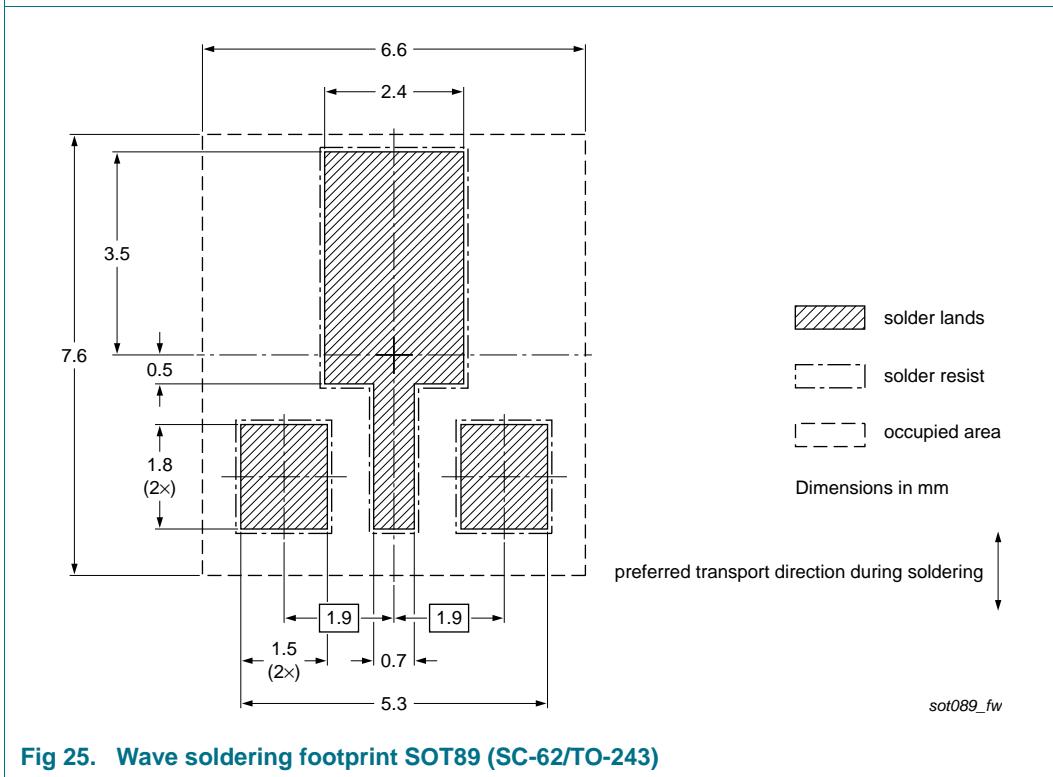


Fig 25. Wave soldering footprint SOT89 (SC-62/TO-243)

